

# SANYO Semiconductors

DATA SHEET

## N-Channel Silicon MOSFET MCH3427 — General-Purpose Switching Device **Applications**

#### **Features**

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 1.8V drive.

### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	۱D		4	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	16	А
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm <sup>2</sup> X0.8mm)	1	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	2.9	4.9		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	ID=2A, VGS=4V		40	52	mΩ
	RDS(on)2	ID=1A, VGS=2.5V		54	76	mΩ
	R <sub>DS</sub> (on)3	ID=0.5A, VGS=1.8V		72	110	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		400		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		92		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		85		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		11		ns
Rise Time	tr	See specified Test Circuit.		75		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		54		ns
Fall Time	tf	See specified Test Circuit.		60		ns

Marking : ZC

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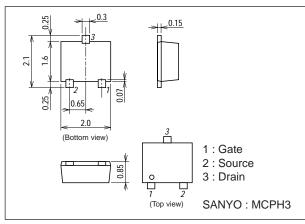
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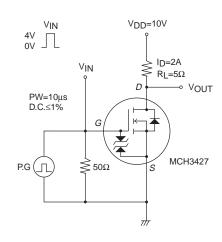
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4A		6		nC
Gate-to-Source Charge	Qgs	VDS=10V, VGS=4V, ID=4A		0.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =4A		2.2		nC
Diode Forward Voltage	VSD	IS=4A, VGS=0		0.87	1.2	V

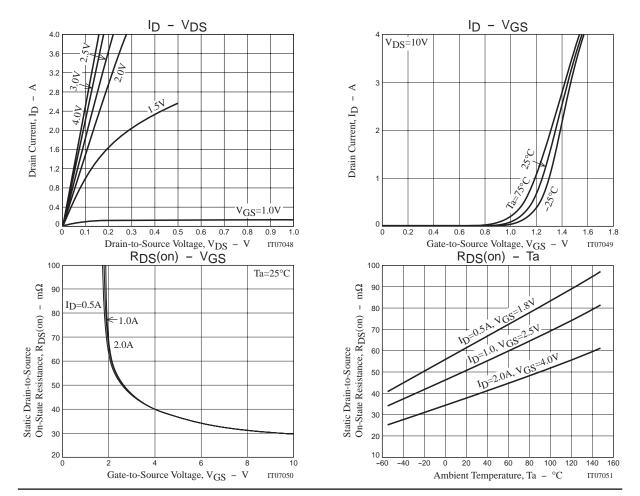
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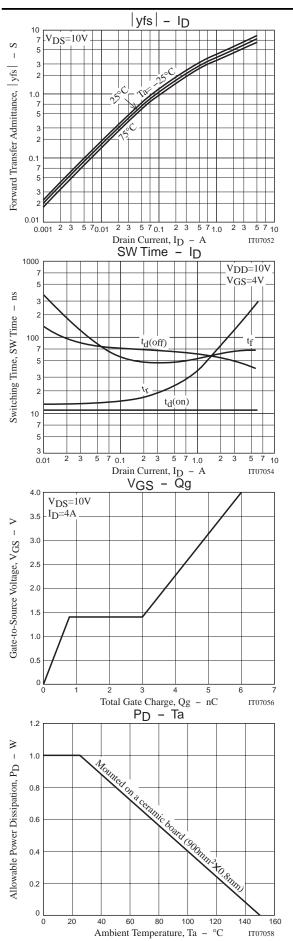
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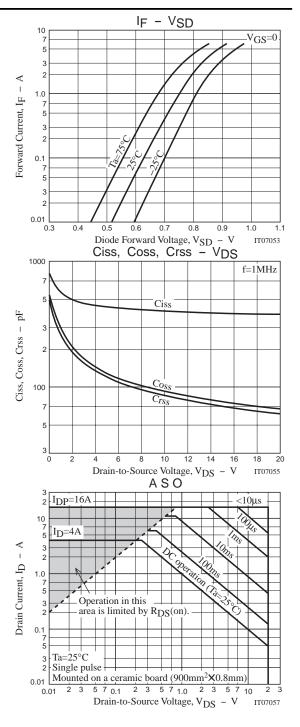


#### **Switching Time Test Circuit**









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